

General Description

The WSD3056DN is the highest performance trench Dual N-Ch MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The WSD3056DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- ☐ Advanced high cell density Trench technology
- ☐ Super Low Gate Charge
- ☐ Excellent CdV/dt effect decline
- ☐ 100% EAS Guaranteed
- ☐ Green Device Available

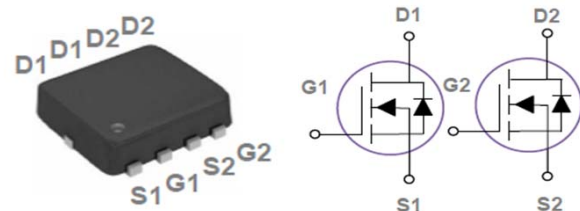
Product Summary

B_{VDS}	$R_{DS(on)}$	I_D
30V	13m Ω	35A

Applications

- ☐ POL Applications
- ☐ MB / VGA / Vcore
- ☐ Load Switch
- ☐ SMPS 2nd SR

DFN3X3 Dual Pin Configuration



Absolute Maximum Ratings @TA=25°C unless otherwise noted

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D	Drain Current (Continuous) *AC	$T_C=25^\circ\text{C}$	35	A
		$T_C=100^\circ\text{C}$	22	
I_{DM}	Drain Current (Pulse) *B		140	A
P_D	Power Dissipation	$T_C=25^\circ\text{C}$	27	W
EAS	Single Pulse Avalanche Energy		13	mJ
$R_{\theta JA}$	Thermal Resistance Junction to ambient		62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case		4.6	$^\circ\text{C/W}$
T_J/T_{STG}	Operating Temperature/ Storage Temperature		-55~150	$^\circ\text{C}$

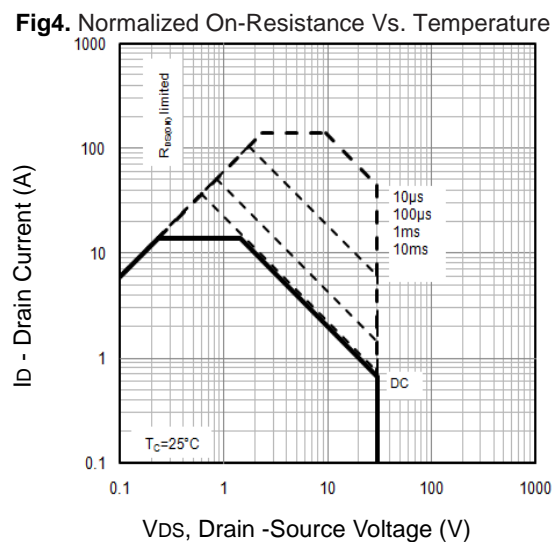
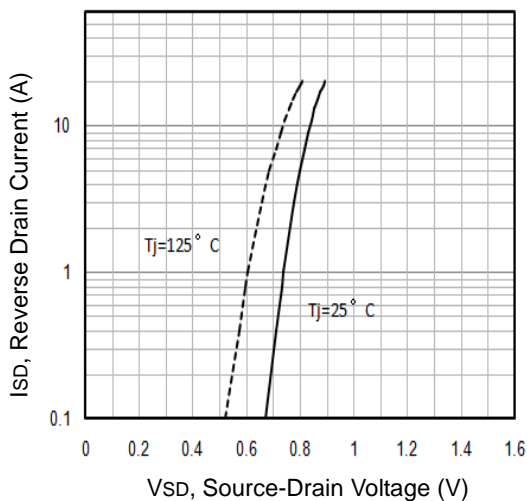
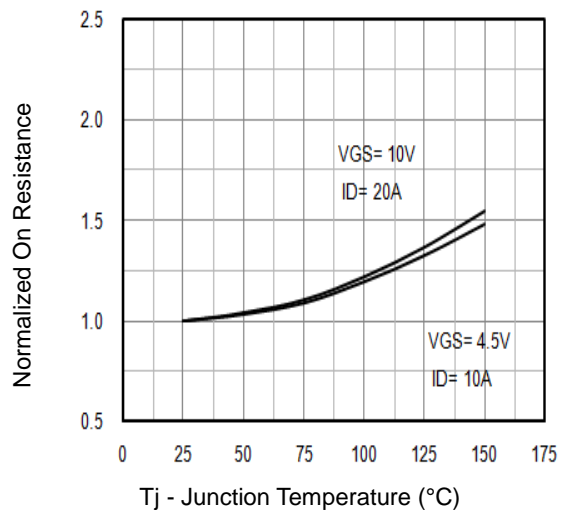
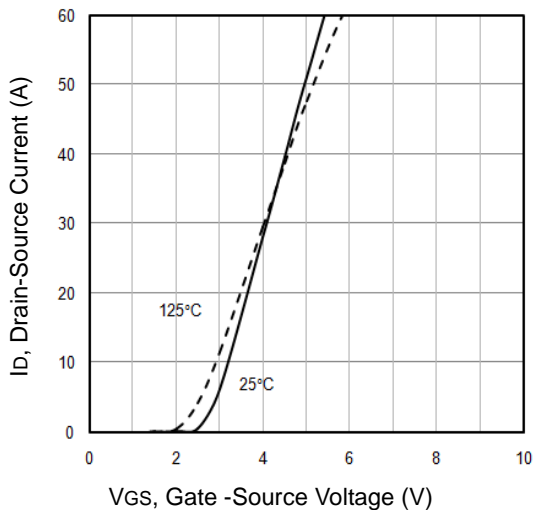
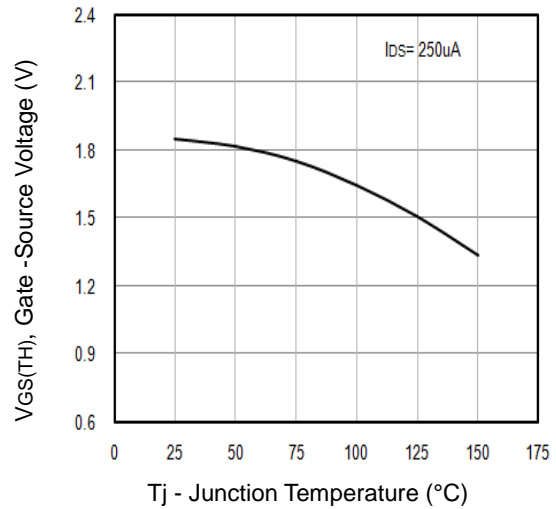
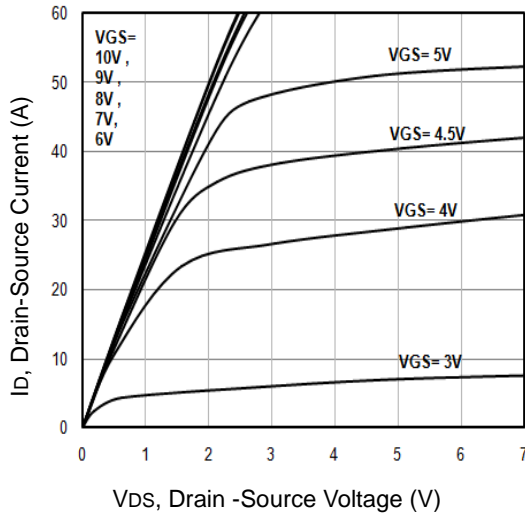
Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30 V, V _{GS} = 0V			1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ±20V, V _{DS} = 0V			100	nA
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _{DS} = 250μA	1.0	1.8	2.5	V
R _{DS(on)}	Drain-Source On-state Resistance	V _{GS} = 10V, I _D = 10A		10	13	mΩ
		V _{GS} = 4.5V, I _D = 8A		14	18	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 5V, I _D = 5A		6		S
Switching						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =5A		7.2		nC
Q _{gs}	Gate-Source Charge			2.3		nC
Q _{gd}	Gate-Drain Charge			3		nC
t _d (on)	Turn-on Delay Time	V _{GS} =10V, V _{DD} =15V, I _D =1A,R _G =6Ω		3.8		ns
t _r	Turn-on Rise Time			10		ns
t _d (off)	Turn-off Delay Time			22		ns
t _f	Turn-off Fall Time			6.6		ns
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.8		Ω
Dynamic						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		620		pF
C _{oss}	Output Capacitance			85		pF
C _{rss}	Reverse Transfer Capacitance			30		pF
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Continuous Source Current	V _G =V _D =0V , Force Current			35	A
I _{SM}	Pulsed Source Current3				70	A
V _{SD}	Diode Forward Voltage	I _{SD} = 1A , V _{GS} =0V			1.2	V

Note :

- 1, Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2, V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=16A., R_G=25 , Starting T_J=25°C.
- 3, The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
- 4, Essentially independent of operating temperature.

Typical Characteristics



Typical Characteristics

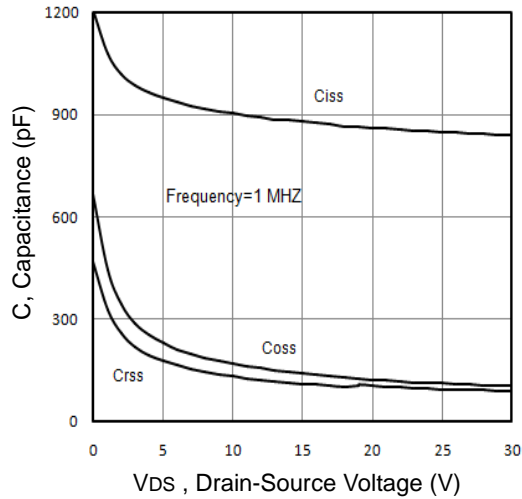


Fig7. Typical Capacitance Vs. Drain-Source Voltage

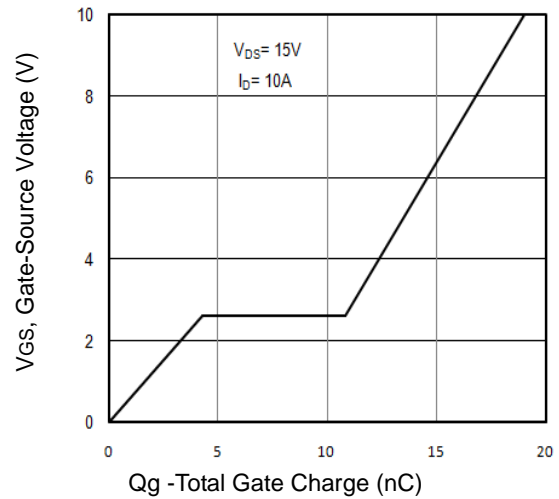


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

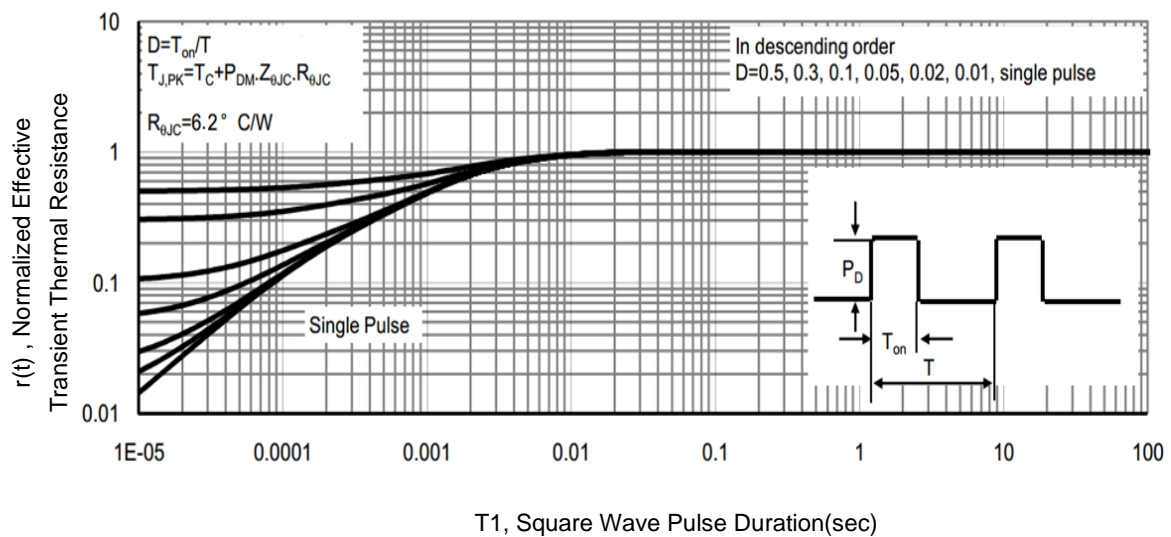


Fig9. T1, Transient Thermal Response Curve

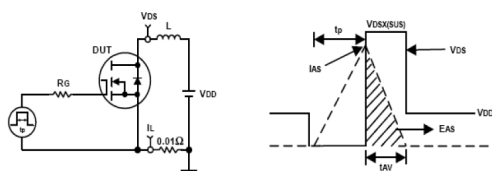


Fig10. Unclamped Inductive Test Circuit and waveforms

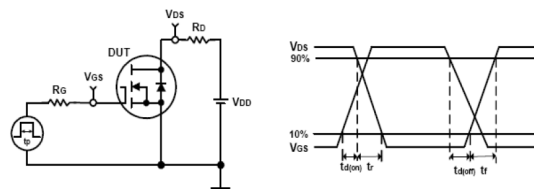
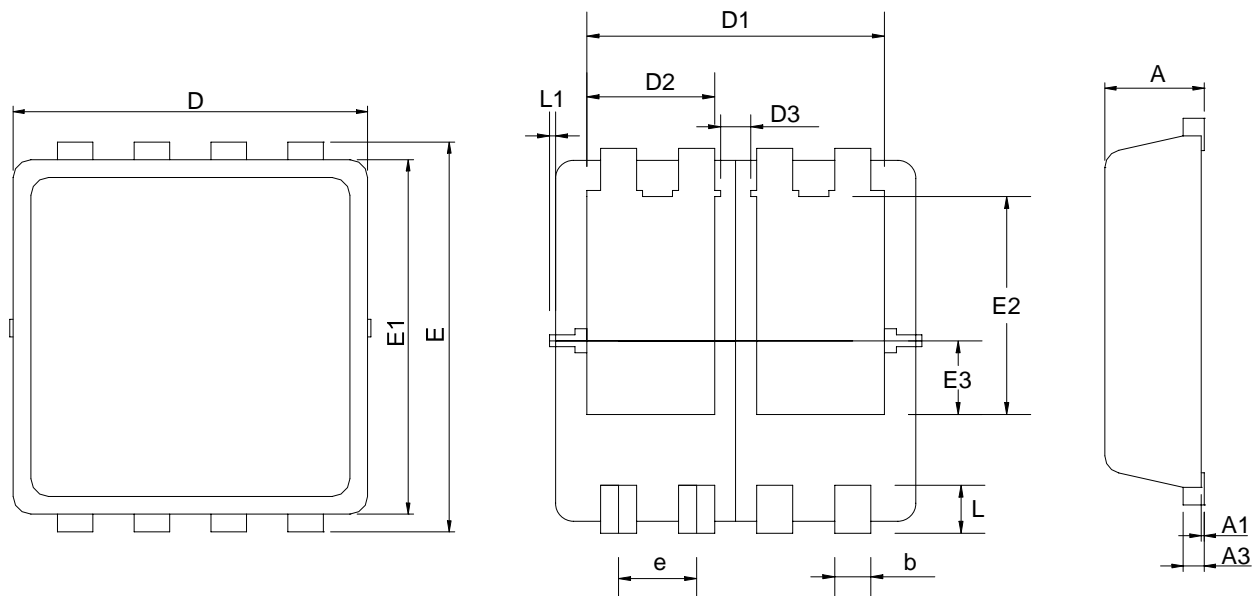


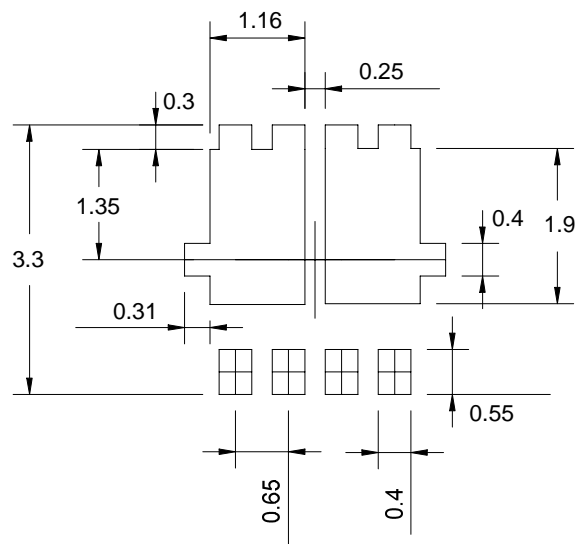
Fig11. Switching Time Test Circuit and waveforms

DFN3x3B-8_EP2



SYMBOL	DFN3x3-8_EP2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
A3	0.10	0.25	0.004	0.010
b	0.24	0.35	0.009	0.014
D	2.90	3.10	0.114	0.122
D1	2.375	2.575	0.094	0.101
D2	0.963	1.163	0.038	0.046
D3	0.175	0.275	0.007	0.011
E	3.10	3.30	0.122	0.130
E1	2.90	3.10	0.114	0.122
E2	1.713	1.913	0.067	0.075
E3	0.425	0.625	0.017	0.025
e	0.65 BSC		0.026 BSC	
L	0.30	0.50	0.012	0.020
L1	0.000	0.100	0.000	0.004

RECOMMENDED LAND PATTERN



UNIT: mm

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